



SSC8205SGSB

Common Drain N-Channel Enhancement Mode MOSFET

➤ **Features**

VDS	VGS	RDSON Typ.	ID
20V	±12V	23mR@4V5	5A
		33mR@2V5	

➤ **Description**

Advanced trench process technology. High density cell design for ultra-low on-resistance. High power and current handling capability. Fully characterized avalanche voltage and current.

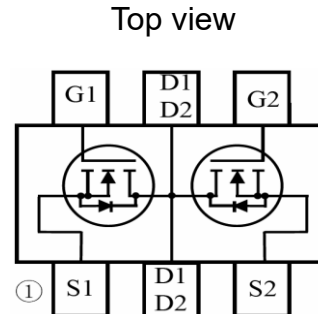
➤ **Applications**

- Li-ion battery protection
- Load switch

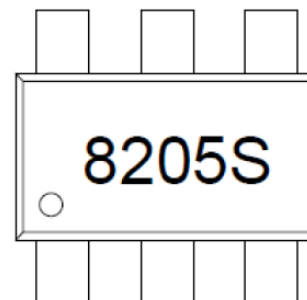
➤ **Ordering Information**

Device	Package	Shipping
SSC8205SGSB	SOT23-6L	3000/Reel

➤ **Pin configuration**



SOT23-6L





➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	20	V
V_{GSS}	Gate-to-Source Voltage	± 12	V
I_D	Continuous Drain Current ^a	5	A
I_{DM}	Pulsed Drain Current ^b	15	A
P_D	Power Dissipation ^c	1.15	W
P_{DSM}	Power Dissipation ^a	0.6	W
T_J	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$
T_{STG}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a		198	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance		108	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with $T_A=25^{\circ}\text{C}$.The value in any given application depends on the user is specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

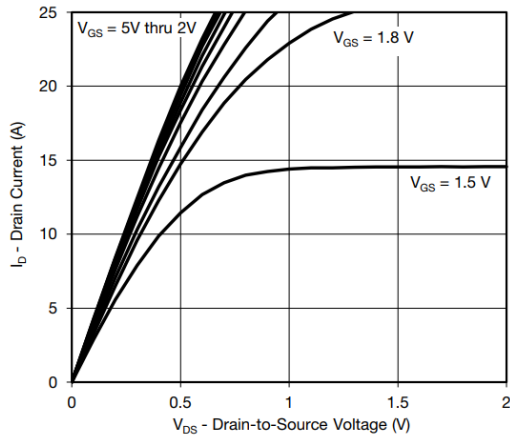


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

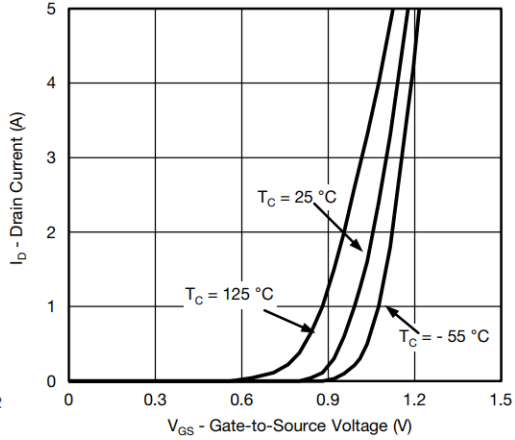
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.65	1	V
$R_{DS(on)}$	Drain-Source On- Resistance	$V_{GS}=4.5V, I_D=3A$		23	27	mR
		$V_{GS}=2.5V, I_D=2A$		33	40	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Source leak current	$V_{GS}=\pm 12V, V_{DS}=0V$			± 100	nA
G_{FS}	Transconductance	$V_{DS}=5V, I_D=4A$		9		S
V_{SD}	Forward Voltage	$V_{GS}=0V, I_S=1A$		0.7	1.3	V
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1MHz$		550		pF
C_{oss}	Output Capacitance			330		
C_{rss}	Reverse Transfer Capacitance			81		
$T_{D(ON)}$	Turn-on delay time			10		
T_r	Rise Time	$V_{GS}=4.5V,$		23		
$T_{D(OFF)}$	Turn-off delay time	$V_{DS}=10V, R_G=1R, I_D=3.5A$		16		
T_f	Fall Time			10		
Q_g	Total Gate charge	$V_{GS}=4.5V, V_{DS}=10V, I_D=4A$		7.7		nC
Q_{gs}	Gate to Source charge			1.1		
Q_{gd}	Gate to Drain charge			2.2		



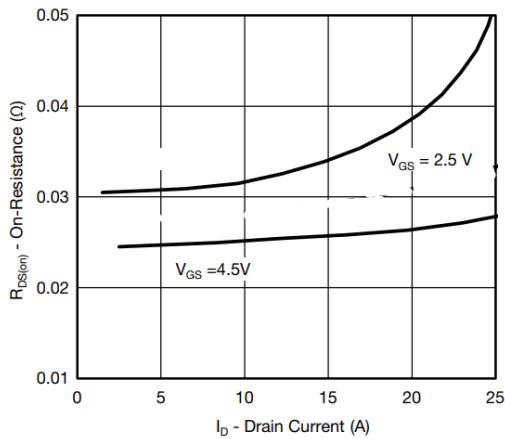
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



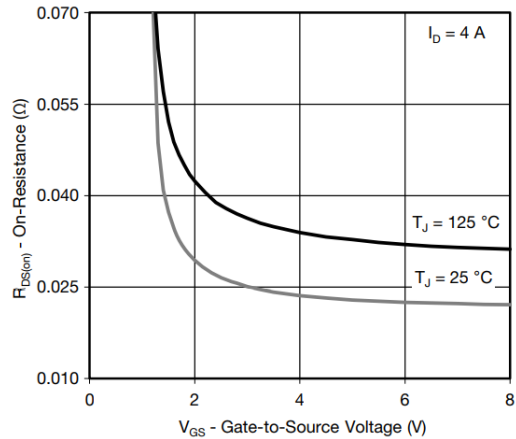
Output Characteristics



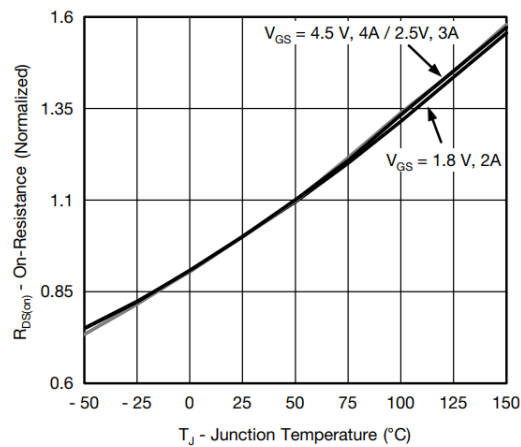
Transfer Characteristics



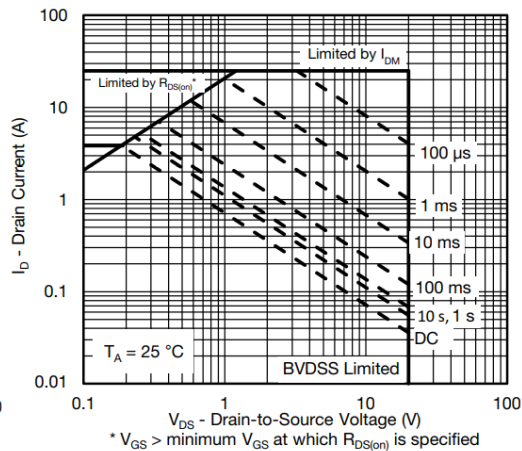
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Gate-to-Source Voltage



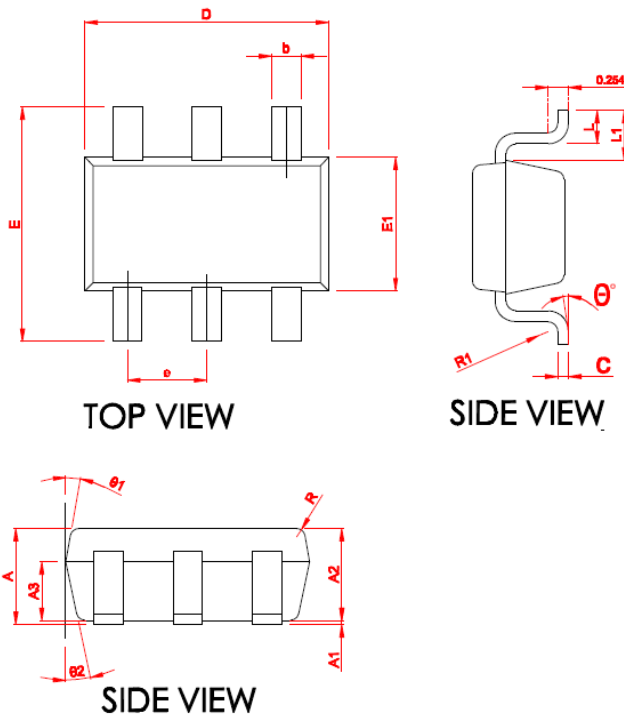
On-Resistance vs. Junction Temperature



Safe Operating Area, Junction-to-Ambient



➤ Package Information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	1.06	1.15	1.24
* A1	0.01	0.05	0.09
* A2	1.05	1.10	1.15
A3	0.65	0.70	0.75
* b	0.30	0.35	0.45
* c	0.117	0.127	0.157
* D	2.87	2.92	2.97
* E	2.72	2.80	2.88
* E1	1.55	1.60	1.65
* e	0.90	0.95	1.00
* L	0.32	0.40	0.48
* L1	0.55	0.60	0.65
R	0.10 REF		
R1	0.12 REF		
* theta	0	--	8°
theta1	8°	10°	12°
theta2	10°	12°	14°

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